28/4

Docket No.: 57454-329

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Masahiro SHIMIZU, et al.

Serial No.: 10/053,543

Filed: January 24, 2002

:Response Under 37 CFR 1.116 - Expedited Procedure

Customer Number: 20277

Confirmation Number: 3990

Group Art Unit: 2814

Examiner: G. Peralta

For: INTEGRATED CIRCUIT HAVING A MEMORY CELL TRANSISTOR WITH A GATE OXIDE LAYER

WHICH IS THICKER THAN THE GATE OXIDE LAYER OF A PERIPHERAL CIRCUIT TRANSISTOR

(As Amended)

Box AF Mail Stop AF Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

 \boxtimes

Transmitted herewith is an Amendment in the above-identified application.

AUG 07

No additional fee is required.

Applicant is entitled to small entity status under 37 CFR 1.27

Also attached:

The fee has been calculated as shown below:

	NO. OF CLAIMS	HIGHEST PREVIOUSLY PAID FOR	EXTRA CLAIMS	RATE	FEE
Total Claims	1	20	0	\$18.00 =	\$0.00
Independent Claims	1	3	0	\$84.00 =	\$0.00
	Multiple claims newly presented			\$0.00	
	Fee for extension o	Fee for extension of time			
					\$0.00
		Total of Above Calculations			\$0.00

Please charge my Deposit Account No. <u>500417</u> in the amount of \$0.00. An additional copy of this transmittal sheet is submitted herewith.

The Commissioner is hereby authorized to charge payment of any fees associated with this communication or credit any overpayment, to Deposit Account No. 500417, including any filing fees under 37 CFR 1.16 for presentation of extra claims and any patent application processing fees under 37 CFR 1.17.

Respectfully submitted,

MCDERMOTT, WILL & EMERY

Registration No. 26,106

600 13th Street, N.W. Washington, DC 20005-3096 (202) 756-8000 AJS:lnm Facsimile: (202) 756-8087

Date: August 7, 2003

Docket No.: 57454-329 PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Masahiro SHIMIZU, et al

Serial No.: 10/053,543

Filed: January 24, 2002

: RESPONSE UNDER 37 CFR 1.116 : EXPEDITED PROCEDURE

: Customer Number: 20277: Confirmation Number: 3990

: Group Art Unit: 2814 : Examiner: G. Peralta

For: INTEGRATED CIRCUIT HAVING A MEMORY CELL TRANSISTOR WITH A GATE OXIDE LAYER WHICH IS THICKER THAN THE GATE OXIDE LAYER OF A PERIPHERAL CIRCUIT TRANSISTOR (As Amended)

AUG 0 7 2003

AMENDMENT UNDER 37 CFR§1.116

Mail Stop AF Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

The following Amendment and Remarks are submitted in response to the Office Action dated May 7, 2003, pursuant to the provisions 37 C.F.R.§1.116.

Amendments to the Claims are reflected in the listing of claims which begins on page 2 of this paper.

Remarks/Arguments begin on page 3 of this paper.